



PE60P80G P-Channel Enhancement Mode Power MOSFET

PE60P80G Description

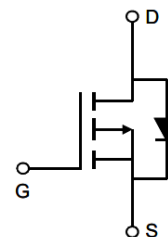
The PE60P80G uses deep trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

PE60P80G General Features

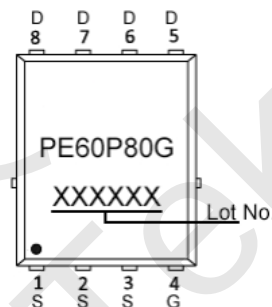
- $V_{DS} = -60V$, $I_D = -80A$
- $R_{DS(ON)} < 15m\Omega$ @ $V_{GS} = -10V$
- $R_{DS(ON)} < 18m\Omega$ @ $V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

PE60P80G Application

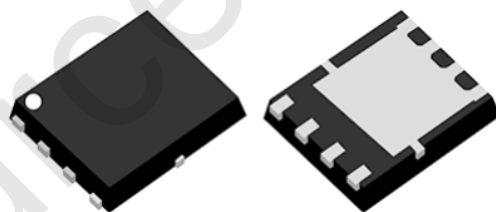
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



DFN5x6-8L

PE60P80G Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-80	A
Drain Current-Continuous (TC=100°C)	I_D	-56	A
Pulsed Drain Current (Note 1)	I_{DM}	-240	A
Maximum Power Dissipation	P_D	100	W
Single Pulsed Avalanche Energy (L=0.1mH)	E_{AS}	218	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

PE60P80G Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	°C/W
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PE60P80G Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-1.8	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-20A$	-	10.5	15	m Ω
		$V_{GS}=-4.5V, I_D=-10A$	-	14	18	m Ω
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-30V, V_{GS}=0V,$ $F=500kHz$	-	2750	-	pF
Output Capacitance	C_{oss}		-	450	-	pF
Reverse Transfer Capacitance	C_{rss}		-	20	-	pF
Gate Resistance	R_g	$V_{GS}=V_{DS}=0V, F=1.0MHz$	-	11	-	Ω
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=-30V, I_D=-20A,$ $V_{GS}=-10V, R_G=3\Omega$	-	20	-	nS
Turn-on Rise Time	t_r		-	25	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	-	nS
Turn-Off Fall Time	t_f		-	30	-	nS
Total Gate Charge	Q_g	$V_{DS}=-30V, I_D=-20A,$ $V_{GS}=-10V$	-	38	-	nC
Gate-Source Charge	Q_{gs}		-	6.9	-	nC
Gate-Drain Charge	Q_{gd}		-	4.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-80	A
Diode Reverse Recovery Time	t_{rr}	$I_F=-10A, dI/dt=100A/\mu s$	-	50	-	nS
Diode Reverse Recovery Charge	Q_{rr}		-	80	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.



PE60P80G Typical Electrical and Thermal Characteristics

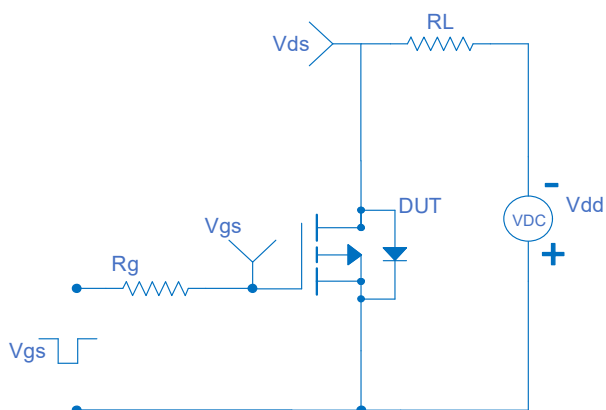


Figure 1 Switching Test Circuit

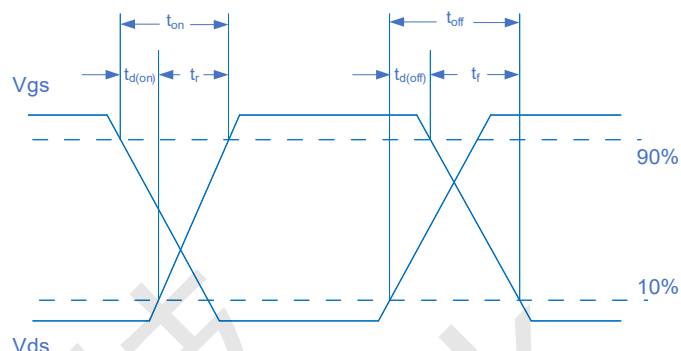


Figure 2 Switching Waveform

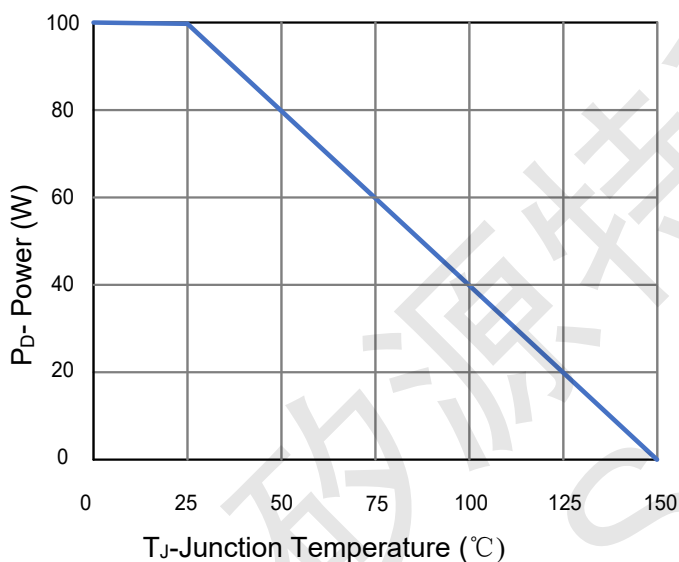


Figure 3 Power De-rating

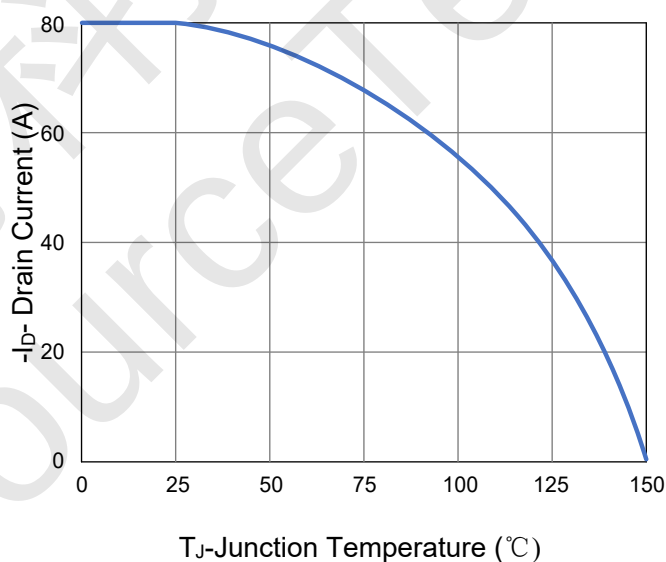


Figure 4 Drain Current

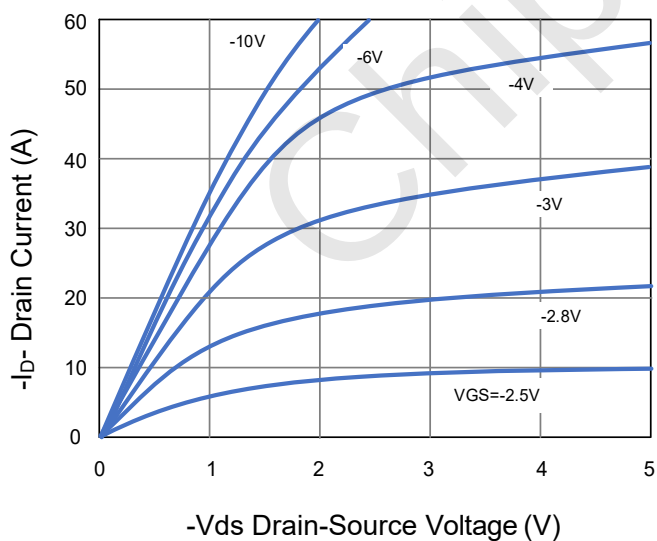


Figure 5 Output Characteristics

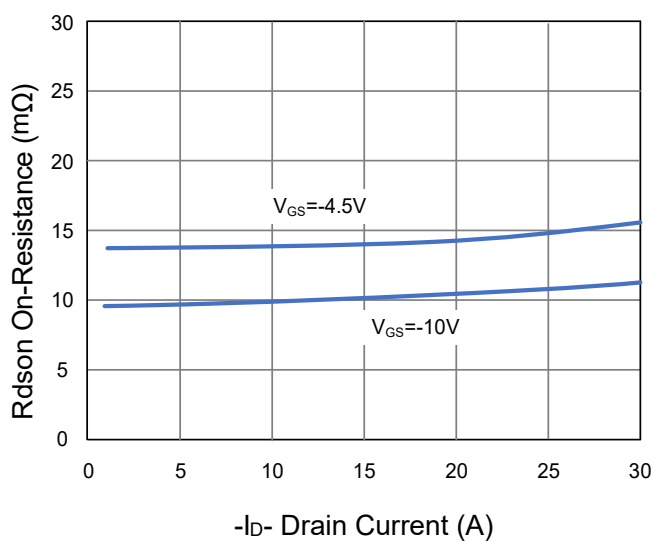
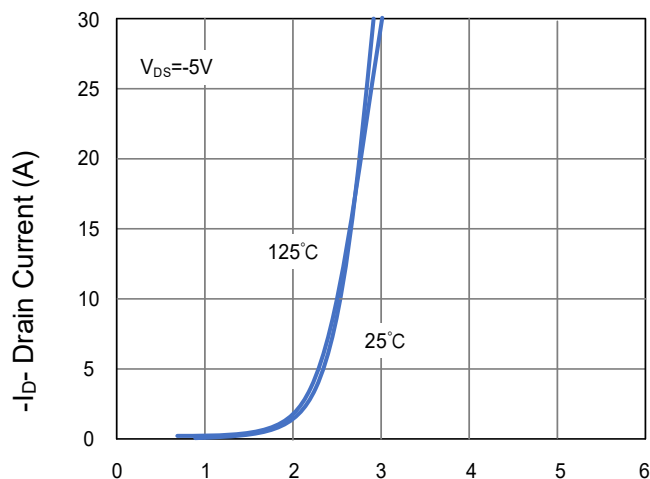
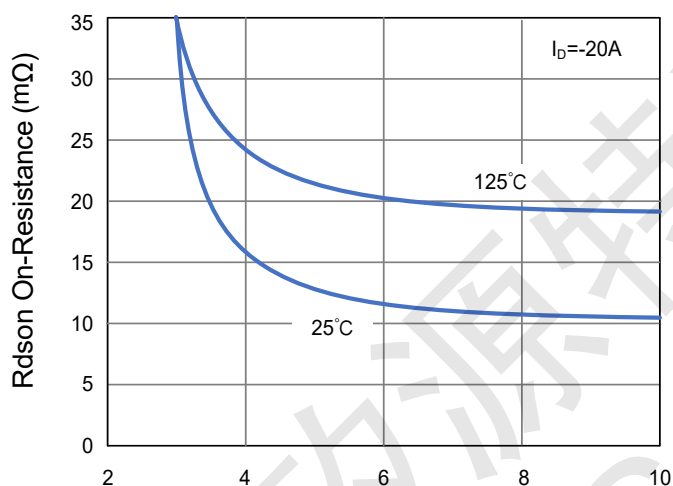


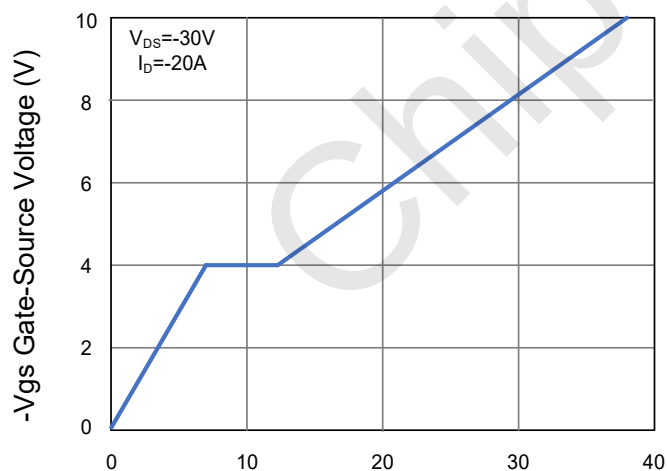
Figure 6 Rdson vs Drain Current



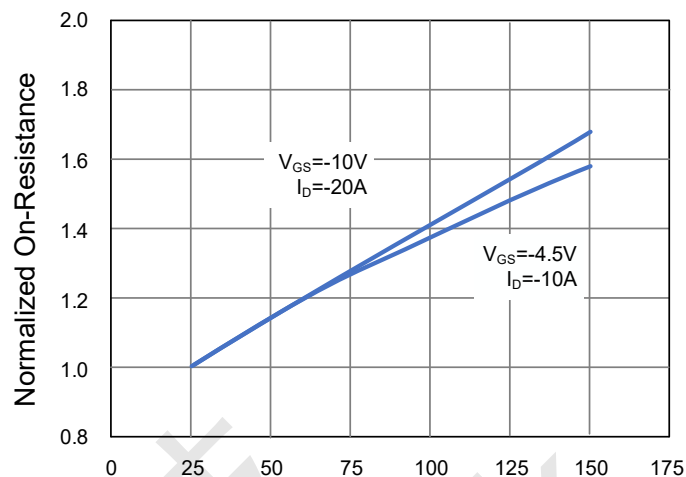
-Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



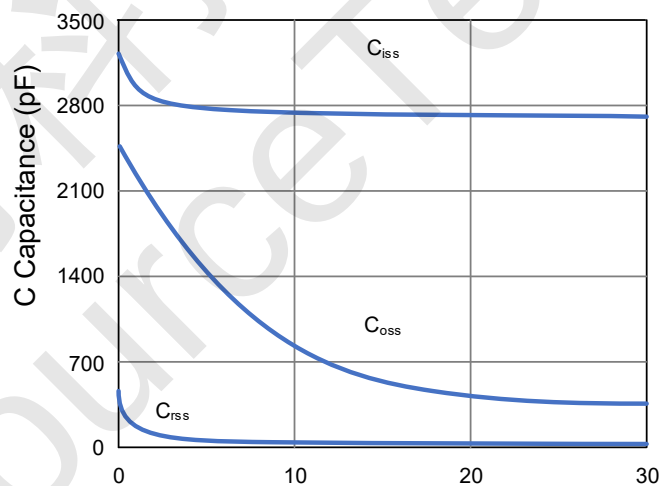
-Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



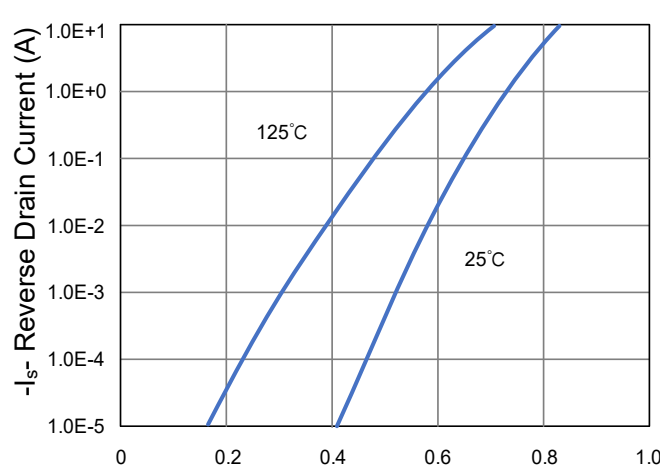
Qg Gate Charge (nC)
Figure 11 Gate Charge



TJ-Junction Temperature(°C)
Figure 8 Rdson vs Junction Temperature



-Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



-Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

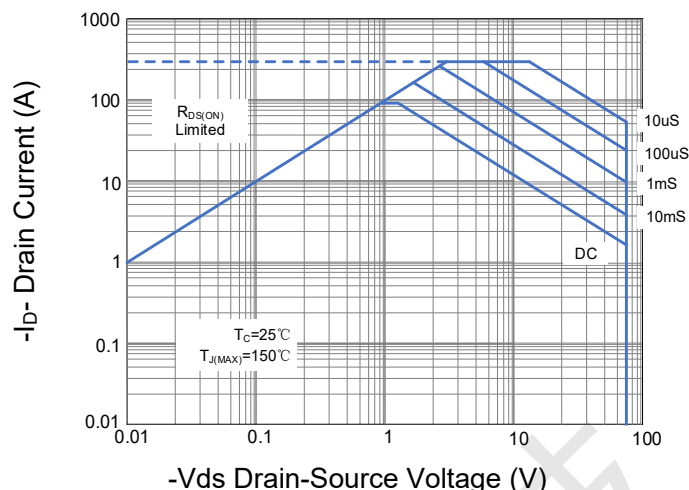


Figure 13 Safe Operation Area

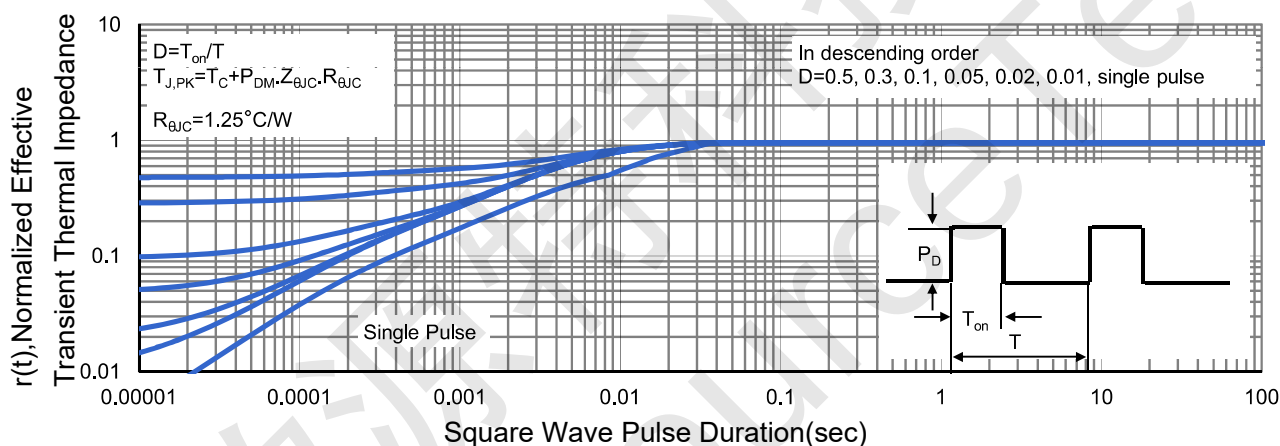
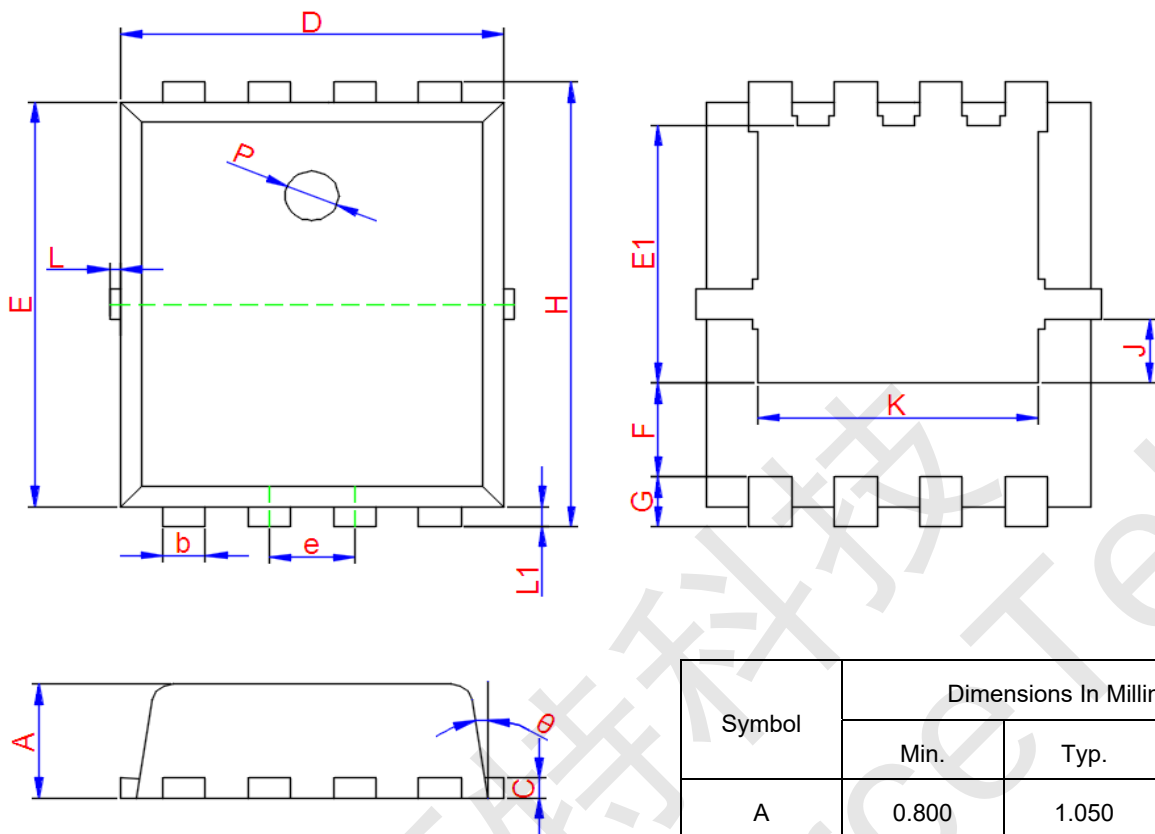


Figure 14 Normalized Maximum Transient Thermal Impedance



PE60P80G DFN5x6-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.800	1.050	1.200
b	0.250	0.350	0.490
c	0.254TYP.		
D	4.800	5.000	5.100
e	1.270TYP.		
E	5.650	5.800	5.900
E1	3.400TYP.		
F	1.300TYP.		
G	0.600TYP.		
H	5.950	6.080	6.200
J	0.950TYP.		
K	4.000TYP.		
L	-	-	0.150
L1	0.100	0.140	0.180
P	1.180TYP.		
θ	6°	10°	14°